

3DG6, 3DG8**NPN Silicon High Frequency Low Power Transistor****Features:**

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications							
			3DG6				3DG8			
			A	B	C	D	A	B	C	D
Total Dissipation	P_{tot}	mW	100 (Ta=25°C)				200 (Ta=25°C)			
Max. Collector Current	I_{CM}	mA	20				30			
Junction Temperature	T_{jm}	°C	175							
Storage Temperature	T_{stg}	°C	-55~+175							
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	30	45	30	45	15	40	40	60
			Ic=0.1mA							
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	15	20	20	30	15	25	25	45
			Ic=0.1mA							
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	$\geq 4 (I_E=0.1 mA)$							
C- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.5 (Ic=10mA, Ib=1mA)							
B- E Saturation Voltage Drop	$V_{BE(sat)}$	V	1.1 (Ic=10mA, Ib=1mA)				1.0 (Ic=10mA, Ib=1mA)			
C-B Leakage Current	I_{CBO}	uA	0.01(V _{CB} =10V)				0.1(V _{CB} =10V)			
C-E Leakage Current	I_{CEO}	uA	0.01(V _{CE} =10V)				0.1(V _{CE} =10V)			
E-B Leakage Current	I_{EBO}	uA	0.01(V _{EB} =1.5V)				0.1(V _{EB} =1.5V)			
DC Current Gain	h_{FE}		25~270 (V _{CE} =10V, Ic=3mA)							
Transition frequency	f_T	MHz	100	150	250	150	150	150	300	300
			V _{CE} =10V, Ic=10mA, f=100MHz				V _{CE} =10V, Ic=3Ma, f=100MHz			

h_{FE} Colored:

Color	Orange	Yellow	Green	Blue	Purple	Gray
h_{FE}	25~40	40~55	55~80	80~120	120~180	180~270

Outline and Dimensions: